## **Sensitive Gate Triacs Series**

#### **Silicon Bidirectional Thyristors**

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO-92 package which is readily adaptable for use in automatic insertion equipment.

#### **Features**

- One-Piece, Injection-Molded Package
- Blocking Voltage to 600 V
- Sensitive Gate Triggering in Four Trigger Modes (Quadrants) for all possible Combinations of Trigger Sources, and especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Improved Noise Immunity (dv/dt Minimum of 10 V/µsec at 110°C)
- Commutating di/dt of 1.6 A/msec at 110°C
- High Surge Current of 8 A
- These are Pb-Free Devices

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage $(T_J = -40 \text{ to } +125^{\circ}\text{C})^{(1)}$ Sine Wave 50 to 60 Hz, Gate Open	V <sub>DRM,</sub> V <sub>RRM</sub>	600	V
On-State RMS Current Full Cycle Sine Wave 50 to 60 Hz (T <sub>C</sub> = 50°C)	I <sub>T(RMS)</sub>	1.0	A
Peak Non-Repetitive Surge Current One Full Cycle, Sine Wave 60 Hz (T <sub>C</sub> = 110°C)	I <sub>TSM</sub>	8.0	Α
Circuit Fusing Considerations (t = 8.3 ms)	I <sup>2</sup> t	0.35	A <sup>2</sup> s
Average Gate Power ( $T_C = 80^{\circ}C$ , $t \le 8.3$ ms)	P <sub>G(AV)</sub>	1.0	W
Peak Gate Current (t $\leq$ 20 $\mu$ s, T <sub>J</sub> = +125°C)	I <sub>GM</sub>	1.0	Α
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

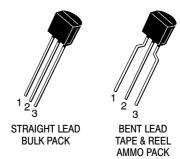


#### **ON Semiconductor**

http://onsemi.com

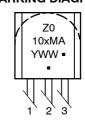
# TRIACS 1.0 AMPERE RMS 600 VOLTS





TO-92 (TO-226AA) CASE 029 STYLE 12

#### MARKING DIAGRAM



x = 3,7,9 Y = Year WW = Work Week ■ = Pb-Free Package

(\*Note: Microdot may be in either location)

PIN ASSIGNMENT		
1	Main Terminal 1	
2	Gate	
3	Main Terminal 2	

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

#### THERMAL CHARACTERISTICS

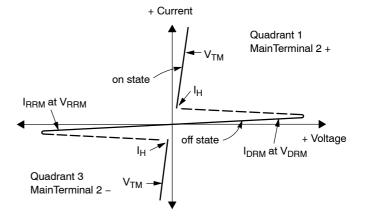
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	50	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	160	°C/W
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	$T_L$	260	°C

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

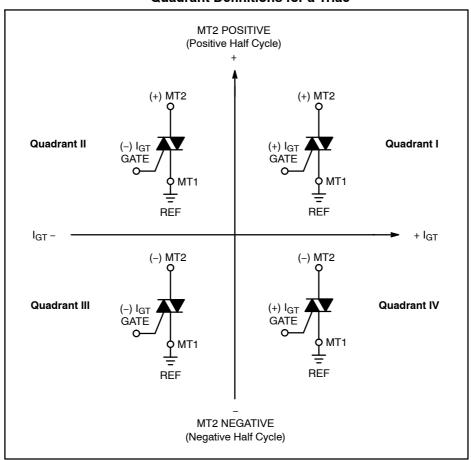
Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS					-1-
$ \begin{array}{ll} \mbox{Peak Repetitive Blocking Current} & T_{J} = 25^{\circ}\mbox{C} \\ \mbox{($V_{D}$ = Rated $V_{DRM}$, $V_{RRM}$; Gate Open)} & T_{J} = +125^{\circ}\mbox{C} \\ \end{array} $	I <sub>DRM</sub> , I <sub>RRM</sub>	- -	- -	5.0 500	μА
ON CHARACTERISTICS					
Peak On–State Voltage ( $I_{TM} = \pm 1.4$ A Peak; Pulse Width $\leq 2.0$ ms, Duty Cycle $\leq 2.0\%$ )	V <sub>TM</sub>	-	-	1.56	٧
Gate Trigger Current (Continuous dc) $ \begin{aligned} &(V_D=12 \text{ Vdc},  R_L=30  \Omega) \\ &MT2(+),  G(+) \\ &MT2(+),  G(-) \\ &MT2(-),  G(-) \\ &MT2(-),  G(+) \end{aligned} $	I <sub>GT</sub>	0.15 0.15 0.15 0.25	- - - -	3.0 3.0 3.0 5.0	mA
Latching Current ( $V_D$ = 12 V, $I_G$ = 1.2 x $I_{GT}$ ) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	IL	- - - -	- - - -	7.0 15 7.0 7.0	mA
Gate Trigger Voltage (Continuous dc) $ \begin{aligned} &(V_D=12 \text{ Vdc, R}_L=30 \ \Omega) \\ &\text{MT2(+), G(+) All Types} \\ &\text{MT2(+), G(-) All Types} \\ &\text{MT2(-), G(-) All Types} \\ &\text{MT2(-), G(+) All Types} \end{aligned} $	V <sub>GT</sub>	- - - -	- - - -	1.3 1.3 1.3 1.3	V
Gate Non–Trigger Voltage ( $V_D$ = 12 V, $R_L$ = 30 $\Omega$ , $T_J$ = 125°C) All Four Quadrants	V <sub>GD</sub>	0.2	-	1.3	V
Holding Current (V <sub>D</sub> = 12 Vdc, Initiating Current = 50 mA, Gate Open)	I <sub>H</sub>	-	-	7.0	mA
DYNAMIC CHARACTERISTICS					
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}$ , $I_{TM} = 0.84 \text{ A}$ , Commutating dv/dt = 1.5 V/ $\mu$ s, Gate Open, $T_J = 110^{\circ}\text{C}$ , $f = 250 \text{ Hz}$ , with Snubber)	di/dt(c)	1.6	-	-	A/ms
Critical Rate of Rise of Off–State Voltage ( $V_D$ = 67% Rated $V_{DRM}$ , Exponential Waveform, Gate Open, $T_J$ = 110°C)	dv/dt	10	30	-	V/µs
Repetitive Critical Rate of Rise of On–State Current, $T_J = 125$ °C Pulse Width = 20 $\mu$ s, IPK <sub>max</sub> = 15 A, diG/dt = 1 A/ $\mu$ s, f = 60 Hz	di/dt	-	-	20	A/μs

### Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

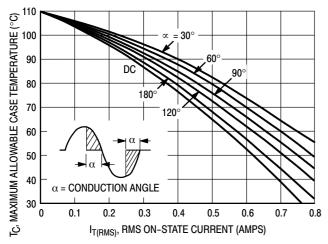


Figure 1. RMS Current Derating

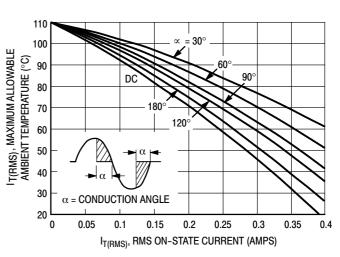


Figure 2. RMS Current Derating

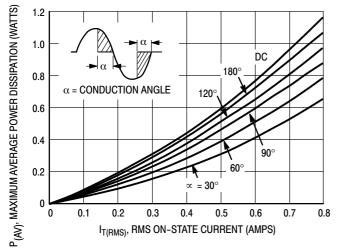


Figure 3. Power Dissipation

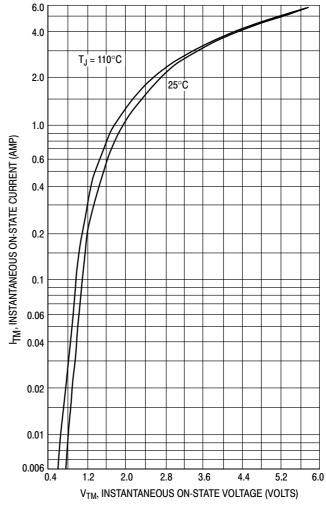
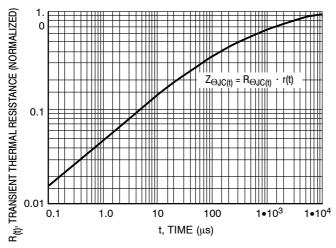


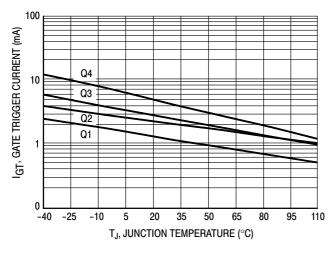
Figure 4. On-State Characteristics



10 TSM, PEAK SURGE CURRENT (AMPS) 5.0 3.0  $T_J = 110^{\circ}C$ 2.0 f = 60 Hz Surge is preceded and followed by rated current 1.0 L 1.0 50 10 30 100 2.0 3.0 5.0 NUMBER OF CYCLES

Figure 5. Transient Thermal Response

Figure 6. Maximum Allowable Surge Current



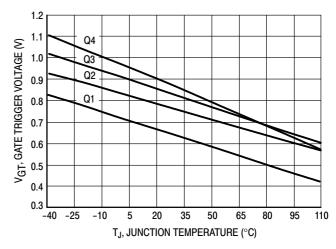
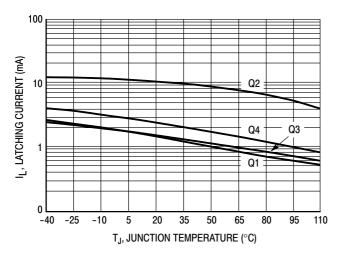


Figure 7. Typical Gate Trigger Current versus Junction Temperature

Figure 8. Typical Gate Trigger Voltage versus Junction Temperature



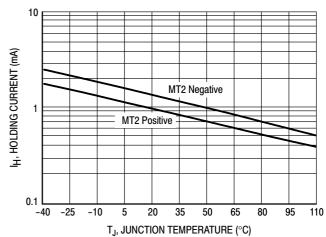
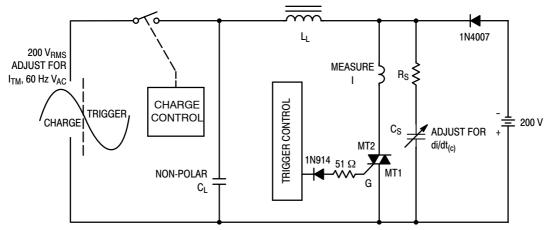


Figure 9. Typical Latching Current versus Junction Temperature

Figure 10. Typical Holding Current versus Junction Temperature



Note: Component values are for verification of rated (di/dt)<sub>c</sub>. See AN1048 for additional information.

Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)<sub>c</sub>

#### ORDERING & SHIPPING INFORMATION: Packaging Options, Device Suffix

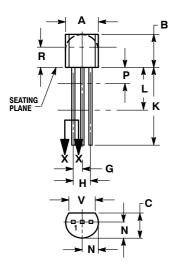
U.S.	Europe Equivalent	Shipping <sup>†</sup>	Description of TO-92 Tape Orientation
	Z0103MARL1G	Radial Tape and Reel (2K/Reel)	Flat side of TO-92 and adhesive tape visible
Z0103MAG		Bulk in Box (5K/Box)	N/A, Bulk
Z0103MARLRPG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape visible
Z0103MARLRFG		Radial Tape and Fan Fold Box (2K/Box)	Round side of TO-92 and adhesive tape on reverse side

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

#### TO-92 (TO-226AA)

CASE 029-11 **ISSUE AM** 



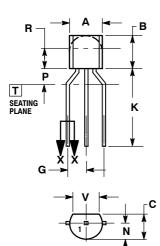
STRAIGHT LEAD **BULK PACK** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



**BENT LEAD** TAPE & REEL AMMO PACK



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND

- DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.45	5.20		
В	4.32	5.33		
С	3.18	4.19		
D	0.40	0.54		
G	2.40	2.80		
J	0.39	0.50		
K	12.70			
N	2.04	2.66		
P	1.50	4.00		
R	2.93			
٧	3.43			

STYLE 12:

PIN 1. MAIN TERMINAL 1

2 GATE

3. MAIN TERMINAL 2

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